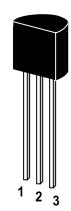
PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into three groups, O, Y and G according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	50	V
Collector Emitter Voltage	-V _{CEO}	50	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	150	mA
Emitter Current	Ι _Ε	150	mA
Power Dissipation	P _{tot}	400	mW
Junction Temperature	Tj	125	°C
Storage Temperature Range	Τs	-55 to +125	°C







Dated : 7/12/2002

ST 2SA1267

Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at -V _{CE} =6V, -I _C =2mA					
Current Gain Group O	h _{FE}	70	-	140	-
Y	h _{FE}	120	-	240	-
G	h _{FE}	200	-	400	-
Collector Cutoff Current					
at -V _{CB} =50V	-I _{CBO}	-	-	0.1	μA
Emitter Cutoff Current					
at -V _{EB} =5V	-I _{EBO}	-	-	0.1	μA
Collector Emitter Saturation Voltage					
at -I _C =100mA, -I _B =10mA	-V _{CE(sat)}	-	0.1	0.3	V
Transition Frequency					
at -V _{CE} =10V, -I _E =1mA	f⊤	80	-	-	MHz
Noise Figure					
at -V _{CE} =6V, -I _C =0.1V, f=1KHZ, R _G =10k Ω	NF	-	1	10	dB
Collector Output Capacitance					
at -V _{CB} =10V, f=1MHz	C _{OB}	-	4	7	pF





